

SKM 400GB124D



SEMITRANS™ 3

Low Loss IGBT Modules

SKM 400GB124D

SKM 400GAL124D

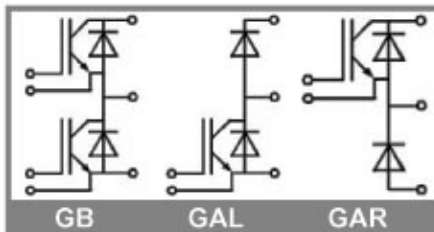
SKM 400GAR124D

Features

- MOS input (voltage controlled)
- N channel, homogeneous Si-structure (NPT- Non punch-through IGBT)
- Low inductance case
- Very low tail current with low temperature dependence
- High short circuit capability, self limiting to $6 \times I_{CNOM}$
- Latch-up free
- Fast & soft inverse CAL Diodes
- Isolated copper baseplate using DCB Direct Copper Bonding Technology without hard mould
- Large clearance (12 mm) and creepage distance (20 mm)

Typical Applications

- Switching (not for lineal use)
- Inverter drives
- UPS



Absolute Maximum Ratings		$T_c = 25\text{ }^\circ\text{C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V_{CES}		1200	V
I_C	$T_c = 25\text{ (80) }^\circ\text{C}$	570 (400)	A
I_{CRM}	$t_p = 1\text{ ms}$	600	A
V_{GES}		± 20	V
T_{vj} (T_{stg})	$T_{OPERATION} \leq T_{stg}$	- 40 ... + 150 (125)	$^\circ\text{C}$
V_{Isol}	AC, 1 min.	2500	V
Inverse diode			
I_F	$T_c = 25\text{ (80) }^\circ\text{C}$	390 (260)	A
I_{FRM}	$t_p = 1\text{ ms}$	600	A
I_{FSM}	$t_p = 10\text{ ms}$; sin.; $T_J = 150\text{ }^\circ\text{C}$	2900	A
Freewheeling diode			
I_F	$T_c = 25\text{ (80) }^\circ\text{C}$	390 (260)	A
I_{FRM}	$t_p = 1\text{ ms}$	600	A
I_{FSM}	$t_p = 10\text{ ms}$; sin.; $T_J = 150\text{ }^\circ\text{C}$	2900	A

Characteristics		$T_c = 25\text{ }^\circ\text{C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 12\text{ mA}$	4,5	5,5	6,5	V
I_{CES}	$V_{GE} = 0$, $V_{CE} = V_{CES}$, $T_J = 25\text{ (125) }^\circ\text{C}$		0,2	0,6	mA
$V_{CE(TO)}$	$T_J = 25\text{ (125) }^\circ\text{C}$		1,1 (1,1)	1,25 (1,25)	V
r_{CE}	$V_{GE} = 15\text{ V}$, $T_J = 25\text{ (125) }^\circ\text{C}$		3,3 (4,3)	4 (5,3)	m Ω
$V_{CE(sat)}$	$I_{Cnom} = 300\text{ A}$, $V_{GE} = 15\text{ V}$, chip level		2,1 (2,4)	2,45 (2,85)	V
C_{res}	under following conditions		22	30	nF
C_{oes}	$V_{GE} = 0$, $V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$		3,3	4	nF
C_{res}			1,2	1,6	nF
L_{CE}				20	nH
R_{CC+EE}	res., terminal-chip $T_c = 25\text{ (125) }^\circ\text{C}$		0,35 (0,5)		m Ω
$t_{d(on)}$	$V_{CC} = 600\text{ V}$, $I_{Cnom} = 300\text{ A}$		85		ns
t_r	$R_{Gon} = R_{Goff} = 5\text{ }\Omega$, $T_J = 125\text{ }^\circ\text{C}$		65		ns
$t_{d(off)}$	$V_{GE} = \pm 15\text{ V}$		680		ns
t_f			56		ns
$E_{on} (E_{off})$			36 (42)		mJ
Inverse diode					
$V_F = V_{EC}$	$I_{Fnom} = 300\text{ A}$; $V_{GE} = 0\text{ V}$; $T_J = 25\text{ (125) }^\circ\text{C}$		2 (1,8)	2,5	V
$V_{(TO)}$	$T_J = (125)^\circ\text{C}$		(1,1)	(1,2)	V
r_T	$T_J = (125)^\circ\text{C}$			(3,5)	m Ω
I_{RRM}	$I_{Fnom} = 300\text{ A}$; $T_J = (125)^\circ\text{C}$		(136)		A
Q_{rr}	$di/dt = \text{A}/\mu\text{s}$		36		μC
E_{rr}	$V_{GE} = \text{V}$				mJ
FWD					
$V_F = V_{EC}$	$I_F = 300\text{ A}$; $V_{GE} = 0\text{ V}$, $T_J = 25\text{ (125) }^\circ\text{C}$		2 (1,8)	2,5	V
$V_{(TO)}$	$T_J = (125)^\circ\text{C}$		(1,1)	(1,2)	V
r_T	$T_J = (125)^\circ\text{C}$			(3,5)	m Ω
I_{RRM}	$I_F = 300\text{ A}$; $T_J = (125)^\circ\text{C}$		(136)		A
Q_{rr}	$di/dt = \text{A}/\mu\text{s}$		36		μC
E_{rr}	$V_{GE} = \text{V}$				mJ
Thermal characteristics					
$R_{th(j-c)}$	per IGBT			0,05	K/W
$R_{th(j-c)D}$	per Inverse Diode			0,125	K/W
$R_{th(j-c)FD}$	per FWD			0,125	K/W
$R_{th(c-s)}$	per module			0,038	K/W
Mechanical data					
M_s	to heatsink M6	3		5	Nm
M_t	to terminals M6	2,5		5	Nm
w				325	g